

forming a laminate on said gate insulating film, comprising:

forming a precursor film for an active layer; and

forming a protective insulating film on said precursor film without using an etching process, the protective insulating film having a thickness of 100 nm or less;

131 implanting a dopant when forming one of an LDD region and a source-drain region of the precursor film for the active layer through the protective insulating film without etching said protective insulating film; and

activating the implanted dopant so that a non-doped portion comprises the active layer.

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8. (Twice amended) The method of making a bottom-gate thin-film transistor comprising:

132 forming a gate electrode on a substrate;

forming a gate insulating film on the gate electrode;

forming a laminate comprising a precursor film for an active layer, and a protective insulating film on the gate insulating film, the protective insulating film having a thickness of 100 nm or less;

implanting a dopant in one of an LDD region and a source-drain region of the precursor film for the active layer through the protective insulating film without etching the protective insulating film; and

activating the implanted dopant so that a non-doped portion comprises the active layer;

wherein, in the laminate forming step, an amorphous silicon film is formed on the gate insulating film, the protective insulating film is formed on a surface of the amorphous silicon film by surface oxidation of the amorphous silicon film, and then the amorphous silicon film is crystallized to form the polysilicon film.

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